

Fabrizio Tamarri

List of Publications by Year in descending order

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Version: 2024-02-01

14
papers

180
citations

1937685

4
h-index

1872680

6
g-index

15
all docs

15
docs citations

15
times ranked

129
citing authors

#	ARTICLE	IF	CITATIONS
1	Micromachined gas calibration sources based on nanometric depth microchannels. <i>Procedia Engineering</i> , 2010, 5, 1344-1347.	1.2	0
2	Material Properties Measurement and Numerical Simulation for Characterization of Ultra-Low-Power Consumption Hotplates. , 2007, , .		4
3	Characterization of MOS Capacitors Fabricated on n-type 4H-SiC Implanted with Nitrogen at High Dose. <i>Materials Science Forum</i> , 2007, 556-557, 639-642.	0.3	4
4	A comparison among different technological processes for the fabrication of polysilicon-based thermoelectric transducers. , 2006, , .		0
5	Ion Implanted p⁺/n Diodes: Post-Implantation Annealing in a Silane Ambient in a Cold-Wall Low-Pressure CVD Reactor. <i>Materials Science Forum</i> , 2006, 527-529, 819-822.	0.3	0
6	Resistance changes due to Cu transport and precipitation during electromigration in submicrometric Al-0.5% Cu lines. <i>Microelectronics Reliability</i> , 1996, 36, 1691-1694.	1.7	13
7	Activation energy in the early stage of electromigration in Al-1% Si/TiN/Ti bamboo lines. <i>Semiconductor Science and Technology</i> , 1995, 10, 255-259.	2.0	122
8	Drawbacks to using NIST electromigration test-structures to test bamboo metal lines. <i>IEEE Transactions on Electron Devices</i> , 1994, 41, 2276-2280.	3.0	18
9	Resistance decay after electromigration as the effect of mechanical stress relaxation. <i>Microelectronics Reliability</i> , 1993, 33, 1841-1844.	1.7	9
10	The Evaluation of the True Test Temperature During Wafer-Level Electromigration Tests. <i>Materials Research Society Symposia Proceedings</i> , 1992, 265, 289.	0.1	2
11	Fabrication of Pt-Polysilicon Thin-Film Thermopiles: A Preliminary Study. , 0, , .		2
12	Room Temperature Annealing Effects on Leakage Current of Ion Implanted p⁺+</sup>+</sup>n 4H-SiC Diodes. <i>Materials Science Forum</i> , 0, 600-603, 1027-1030.	0.3	1
13	Effects of N Implantation before Gate Oxidation on the Performance of 4H-SiC MOSFET. <i>Materials Science Forum</i> , 0, 615-617, 761-764.	0.3	0
14	Fully Ion Implanted Vertical p-i-n Diodes on High Purity Semi-Insulating 4H-SiC Wafers. <i>Materials Science Forum</i> , 0, 717-720, 985-988.	0.3	2